

Title (en)  
SEMICONDUCTOR CIRCUIT DEVICE AND METHOD FOR THE PRODUCTION THEREOF

Title (de)  
HALBLEITERSCHALTUNGSVORRICHTUNG UND VERFAHREN ZUR HERSTELLUNG

Title (fr)  
CIRCUIT A SEMI-CONDUCTEUR ET PROCEDE DE FABRICATION DUDIT CIRCUIT

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Application  
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Abstract (en)  
[origin: DE19726881A1] The invention relates to a monolithic integrated semiconductor circuit device (1), comprising a semiconductor substrate (2), in which or on which several circuit elements are configured, electrically interconnected and optionally connected to other contact points, especially those arranged on the edge of the semiconductor substrate (2), by means of conductor patterns (4, 5, 6), which are included in several contact planes (Poly-Si, M1, M2, M3), beginning with a first (poly-Si) plane which is the closest to the main surface (3) of the semiconductor substrate (2) and ranging to a final contact plane (M3). A protection facility consisting of interruptable fuses (8) or connectable anti-fuses is configured at least in sections on the basis of the conductor pattern (6) of the penultimate contact plane (M2). The invention also relates to a method for producing such monolithic integrated semiconductor circuit device (1).

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